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Investigations on hydrophilic and hydrophobic silicon (100) wafer surfaces by X-ray photoelectron and high-resolution electron energy loss-spectroscopy

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381	Effects in Silicon Explained by Atomic Hydrogen. <b>1987</b> , 104, 291		18
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379	Photoelectron Spectroscopy of the Adsorption of Amino Acids on Surfaces: Glycine on Si(O <sub>2</sub> ). <b>1987</b> , 35, 586-589		23
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377	High-resolution electron microscopy and scanning tunneling microscopy of native oxides on silicon. <b>1987</b> , 237, 630-3		52
376	A preliminary study of impurities and defects in Si-MBE layers. <b>1987</b> , 81, 326-331		14
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